

Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

1. (Currently Amended) A semiconductor device comprising an element forming region where wiring is specified with the boundary on the main surface of a semiconductor substrate and a dummy region, where wiring is not formed, is adjacent to said boundary is not formed,

wherein said dummy region has at least two dummy pattern groups, a groups each including a plurality of conductive islands formed with the a same conductive layer same as said wiring, the conductive islands within each dummy pattern group have of the same shape and same size occupying the surface are placed, in each dummy pattern group, in isolation in both row and column directions with the insulation film, and are arranged on the main surface in both row and column directions as mutually isolated islands, surrounded via an insulation film, and the sizes of a plurality of said conductive islands in the row and/or column direction are different among the different ones of said at least two dummy pattern groups.

Claims 2-21. (Canceled without prejudice or disclaimer)

22. (New) A semiconductor device comprising:

a semiconductor element formed in a semiconductor substrate,

a first insulation film formed over said semiconductor element, and

a first, second and third wirings formed over said first insulation film,
respectively,

wherein said third wiring is electrically connected with said semiconductor
element,

wherein said first and second wirings are not electrically connected with said
semiconductor element, and

wherein a planar size of said first wiring is larger than a planar size of said
second wiring.

23. (New) A semiconductor device according to claim 22,
wherein said first, second and third wirings are formed at a same layer.

24. (New) A semiconductor device according to claim 22,
wherein said first and second wirings are arranged in the row and/or column
direction.

25. (New) A semiconductor device according to claim 22,
wherein said first and second wirings are a dummy wiring, respectively.

26. (New) A semiconductor device according to claim 22, further
comprising:

a second insulation film formed over said first insulation film and said first,
second and third wirings,

wherein said second insulation film is substantially flattened.

27. (New) A semiconductor device according to claim 22,
wherein said first, second and third wirings are formed of aluminum or
copper, respectively.

28. (New) A semiconductor device comprising:
a semiconductor element formed in a semiconductor substrate,
a first insulation film formed over said semiconductor element, and
a first and second dummy wirings formed over said first insulation film,
respectively,
wherein said first and second dummy wirings are not electrically connected
with said semiconductor element, and
wherein a planar size of said first wiring is larger than a planar size of said
second wiring.